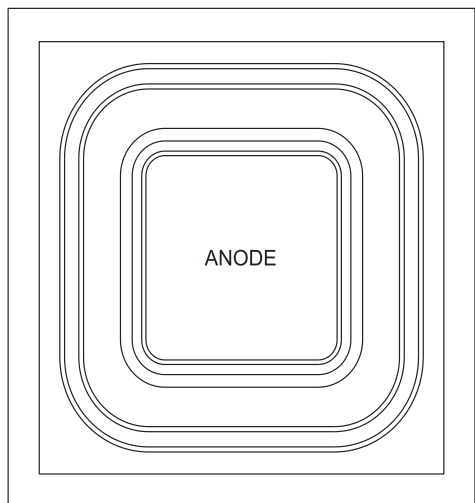


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	16 x 16 MILS
Die Thickness	9.0 MILS
Anode Bonding Pad Area	6.5 x 6.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE CATHODE

R0

145 Adams Avenue
Hauppauge, NY 11788 USA
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GROSS DIE PER 4 INCH WAFER

45,050

PRINCIPAL DEVICE TYPES

CMPD2003
CMPD2004
1N3070
CMDD2003
CMDD2004

The Typical Electrical Characteristics data for this chip is currently being revised.

For the latest updated data for this Chip Process, please visit our website at:

www.centalsemi.com/chip

R1 (1-August 2002)